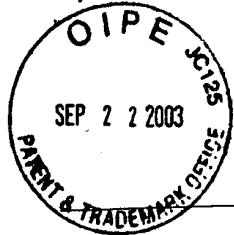


2818



PATENT

Case Docket No. IMEC279.001AUS
Date: September 18, 2003

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant(s) : Van Houdt, et al.

Appl. No. : 10/603,426

Filed : June 24, 2003

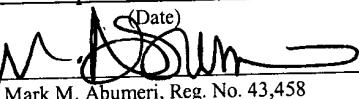
For : MULTIBIT NON-VOLATILE
MEMORY AND METHOD

Examiner : Unassigned

Group Art Unit : 2818

I hereby certify that this correspondence and all marked attachments are being deposited with the United States Postal Service as first class mail in an envelope addressed to: Commissioner for Patents, P.O. Box 1450, Alexandria, VA 22313-1450, on

September 18, 2003


Mark M. Abumeri, Reg. No. 43,458

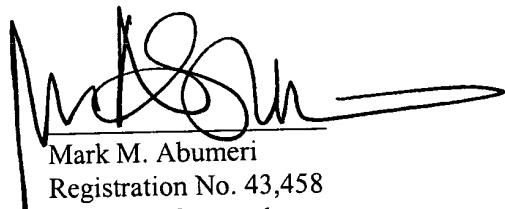
TRANSMITTAL LETTER

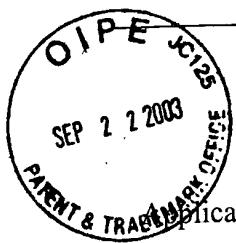
Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

Dear Sir:

Enclosed for filing in the above-identified application are:

- An Information Disclosure Statement.
- A PTO Form 1449 with twenty-two (22) references.
- The Commissioner is hereby authorized to charge any additional fees which may be required, or credit any overpayment, to Account No. 11-1410.
- Return prepaid postcard.


Mark M. Abumeri
Registration No. 43,458
Attorney of Record
Customer No. 20,995
(619) 235-8550



INFORMATION DISCLOSURE STATEMENT

Applicant : Van Houdt, et al.
App. No. : 10/603,426
Filed : June 24, 2003
For : MULTIBIT NON-VOLATILE MEMORY
AND METHOD
Examiner : Unassigned
Group Art Unit : 2818

Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

Dear Sir:

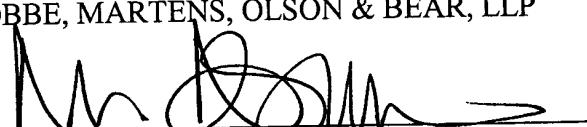
Enclosed is form PTO-1449 listing twenty-two (22) references that are also enclosed.

This Information Disclosure Statement is being filed with an RCE or within three months of the filing date of this application and no fee is required in accordance with 37 C.F.R. § 1.97(b)(1), (b)(2), or (b)(4).

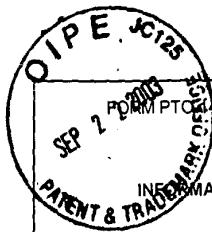
Respectfully submitted,

KNOBBE, MARTENS, OLSON & BEAR, LLP

By:


Mark M. Abumeri
Registration No. 43,458
Attorney of Record
Customer No. 20,995
(619) 235-8550

Dated: September 18, 2003



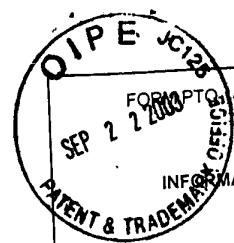
| | | | |
|--|--|------------------------------------|-------------------------------|
| U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE | | ATTY. DOCKET NO. IMEC279.001AUS | APPLICATION NO. 10/603,426 |
| INFORMATION DISCLOSURE STATEMENT BY APPLICANT | | | |
| (USE SEVERAL SHEETS IF NECESSARY) | | | |
| APPLICANT Van Houdt, et al. | | FILING DATE June 24, 2003 | |
| | | GROUP 2818 | |

| U.S. PATENT DOCUMENTS | | | | | | |
|-----------------------|-----------------|----------|----------------------|-------|----------|------------------------------|
| EXAMINER INITIAL | DOCUMENT NUMBER | DATE | NAME | CLASS | SUBCLASS | FILING DATE (IF APPROPRIATE) |
| 1 | 4,794,565 | 12/27/88 | Wu, et al. | | | |
| 2 | 5,278,439 | 01/11/94 | Ma, et al. | | | |
| 3 | 5,280,446 | 01/18/94 | Ma, et al. | | | |
| 4 | 5,284,784 | 02/08/94 | Manley | | | |
| 5 | 5,338,952 | 08/16/94 | Yamauchi | | | |
| 6 | 5,394,360 | 02/28/95 | Fukumoto | | | |
| 7 | 5,538,811 | 12/10/96 | Van Houdt, et al. | | | |
| 8 | 5,841,697 | 11/24/98 | Van Houdt, et al. | | | |
| 9 | 6,044,015 | 03/28/00 | Van Houdt, et al. | | | |
| 10 | 6,366,500 B1 | 04/02/02 | Ogura, et al. | | | |
| 11 | 6,580,120 B1 | 06/17/03 | Haspeslagh | | | |
| 12 | 2002/0005545 A1 | 01/17/02 | Widdershoven, et al. | | | |

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|--------------------------|-----------------|----------|---------|-------|----------|-------------|
| EXAMINER INITIAL | DOCUMENT NUMBER | DATE | COUNTRY | CLASS | SUBCLASS | TRANSLATION |
| | | | | | | YES NO |
| 13 | EP 1 096 572 A1 | 05/02/01 | EUROPE | | | |

| EXAMINER INITIAL | OTHER DOCUMENTS (INCLUDING AUTHOR, TITLE, DATE, PERTINENT PAGES, ETC.) | |
|------------------|---|--|
| 14 | Esquivel, et al., "High density contactless, self aligned EPROM cell array technology", IEDM Tech. Dig., pp. 592-595, (1986). | |
| 15 | Hayashi, et al., "Twin MONOS cell with dual control gates", IEEE, presented at the 2000 Symposium on VLSI Technology Digest of Technical Papers, pp. 122-123, (2000). | |
| 16 | <i>Microlithography, Science and Technology</i> , Sheats, et al., Eds., Marcel Dekker, Inc., New York, New York, pp. 515-565 and 615-644, (1998). | |
| 17 | Miyawaki, et al., "A new erasing and row decoding scheme for low supply voltage operation 16-Mb/64-Mb flash memories", IEEE Journal of Solid-State Circuits, vol. 27, no. 4, pp. 583-588, (April 1992). | |
| 18 | Tanaka, et al., "A quick intelligent page-programming architecture and a shielded bitline sensing method for 3V-only NAND flash memory", IEEE Journal of Solid-State Circuits, vol. 29, no. 11, pp. 1366-1373, (November 1994). | |
| 19 | Van Houdt, et al., "A 5-volt-only fast-programming flash EEPROM cell with a double polysilicon split-gate structure", presented at the 11 th IEEE Non-volatile Semiconductor Memory Workshop, (February 1991). | |

| EXAMINER | DATE CONSIDERED |
|--|-----------------|
| *EXAMINER: INITIAL IF CITATION CONSIDERED, WHETHER OR NOT CITATION IS IN CONFORMANCE WITH MPEP 609; DRAW LINE THROUGH CITATION IF NOT IN CONFORMANCE AND NOT CONSIDERED, INCLUDE COPY OF THIS FORM WITH NEXT COMMUNICATION TO APPLICANT. | |



SHEET 2 OF 2

| | | |
|---|------------------------------------|-------------------------------|
| U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE INFORMATION DISCLOSURE STATEMENT BY APPLICANT (USE SEVERAL SHEETS IF NECESSARY) | ATTY. DOCKET NO. IMEC279.001AUS | APPLICATION NO. 10/603,426 |
| | APPLICANT Van Houdt, et al. | |
| | FILING DATE June 24, 2003 | GROUP 2818 |

| EXAMINER INITIAL | OTHER DOCUMENTS (INCLUDING AUTHOR, TITLE, DATE, PERTINENT PAGES, ETC.) |
|------------------|--|
| 20 | Van Houdt, et al., "Analysis of the enhanced hot-electron injection in split-gate transistors useful for EEPROM applications", IEEE Transactions on Electron Devices, vol. 39, no. 5, pp. 1150-1156, (May 1992). |
| 21 | Van Houdt, et al., "HIMOS-A high efficiency flash E2PROM cell for embedded memory applications", IEEE Transactions on Electron Devices, vol. 40, no. 12, pp. 2255-2263, (December 1993). |
| 22 | Yamauchi, et al., "A 5V-only virtual ground flash cell with an auxilliary gate for high density and high speed application", IEDM Tech. Dig., p. 319-322, (1991). |

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| EXAMINER | DATE CONSIDERED |
| *EXAMINER: INITIAL IF CITATION CONSIDERED, WHETHER OR NOT CITATION IS IN CONFORMANCE WITH MPEP 609; DRAW LINE THROUGH CITATION IF NOT IN CONFORMANCE AND NOT CONSIDERED, INCLUDE COPY OF THIS FORM WITH NEXT COMMUNICATION TO APPLICANT. | |